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<ul> <li>Member of Texas Instruments' Widebus™</li> <li>Family</li> </ul>	DGG PACKAGE (TOP VIEW)		
<ul> <li>■ UBT<sup>™</sup> Transceiver Combines D-Type Latches and D-Type Flip-Flops for Operation in Transparent, Latched, or Clocked Mode</li> </ul>	1 <u>OEAB</u> [ 1 1OEBA [ 2 V <sub>CC</sub> [ 3 1A1 [ 4	64 CLK 63 1LEAB 62 1LEBA 61 ERC	
<ul> <li>TI-OPC™ Circuitry Limits Ringing on Unevenly Loaded Backplanes</li> </ul>	GND [5 1A2 [6	60 GND 59 1B1	
<ul> <li>OEC<sup>™</sup> Circuitry Improves Signal Integrity and Reduces Electromagnetic Interference</li> </ul>	1A3 [] 7 GND [] 8	58 ] 1B2 57 ] GND	
<ul> <li>Bidirectional Interface Between GTLP</li> <li>Signal Levels and LVTTL Logic Levels</li> </ul>	1A4 <b>[</b> ]9 GND <b>[</b> ]10	56 ] 1B3 55 ] 1B4	
<ul> <li>Partitioned as Two 8-Bit Transceivers With Individual Latch Timing and Output Control, but With a Common Clock</li> </ul>	1A5 [] 11 GND [] 12 1A6 [] 13	54 ] 1B5 53 ] GND 52 ] 1B6	
<ul> <li>LVTTL Interfaces Are 5-V Tolerant</li> <li>High-Drive GTLP Outputs (100 mA)</li> </ul>	1A7 🛮 14 V <sub>CC</sub> 🗓 15	51 1B7 50 V <sub>CC</sub>	
LVTTL Outputs (–24 mA/24 mA)	1A8 🛮 16 2A1 🗓 17	49 🛘 1B8 48 🖟 2B1	
<ul> <li>Variable Edge-Rate Control (ERC) Input Selects GTLP Rise and Fall Times for Optimal Data-Transfer Rate and Signal Integrity in Distributed Loads</li> </ul>	GND [] 18 2A2 [] 19 2A3 [] 20 GND [] 21	47 ] GND 46 ] 2B2 45 ] 2B3 44 ] GND	
<ul> <li>I<sub>off</sub>, Power-Up 3-State, and BIAS V<sub>CC</sub> Support Live Insertion</li> </ul>	2A4 [ 22 2A5 [ 23	43	
<ul> <li>Bus Hold on A-Port Data Inputs</li> <li>Distributed V<sub>CC</sub> and GND Pins Minimize</li> </ul>	GND [ 24 2A6 [ 25 GND [ 26	41 V <sub>REF</sub> 40 2B6 39 GND	
<ul> <li>High-Speed Switching Noise</li> <li>Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II</li> </ul>	2A7 [ 27 V <sub>CC</sub> [ 28 2A8 [ 29	38 ] 2B7 37 ] 2B8 36 ] BIAS V <sub>CC</sub>	
<ul> <li>ESD Protection Exceeds JESD 22</li> <li>2000-V Human-Body Model (A114-A)</li> <li>200-V Machine Model (A115-A)</li> </ul>	GND [ 30 20EAB [ 31 20EBA [ 32	35 ] 2LEAB 34 ] 2LEBA 33 ] OE	

### description

The SN74GTLPH1655 is a high-drive, 16-bit UBT<sup>TM</sup> transceiver that provides LVTTL-to-GTLP and GTLP-to-LVTTL signal-level translation. It is partitioned as two 8-bit transceivers and allows for transparent, latched, and clocked modes of data transfer. The device provides a high-speed interface between cards operating at LVTTL logic levels and a backplane operating at GTLP signal levels. High-speed (about three times faster than standard LVTTL or TTL) backplane operation is a direct result of GTLP's reduced output swing (<1 V), reduced input threshold levels, improved differential input, OEC<sup>TM</sup> circuitry, and TI-OPC<sup>TM</sup> circuitry. Improved GTLP OEC and TI-OPC circuits minimize bus-settling time and have been designed and tested using several backplane models. The high drive allows incident-wave switching in heavily loaded backplanes with equivalent load impedance down to 11 Ω.



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- 1000-V Charged-Device Model (C101)



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### description (continued)

GTLP is the Texas Instruments (TI<sup>TM</sup>) derivative of the Gunning Transceiver Logic (GTL) JEDEC standard JESD 8-3. The ac specification of the SN74GTLPH1655 is given only at the preferred higher noise-margin GTLP, but the user has the flexibility of using this device at either GTL ( $V_{TT} = 1.2 \text{ V}$  and  $V_{REF} = 0.8 \text{ V}$ ) or GTLP ( $V_{TT} = 1.5 \text{ V}$  and  $V_{REF} = 1 \text{ V}$ ) signal levels.

Normally, the B port operates at GTLP signal levels. The A-port and control inputs operate at LVTTL logic levels, but are 5-V tolerant and are compatible with TTL and 5-V CMOS inputs. V<sub>REF</sub> is the B-port differential input reference voltage.

This device is fully specified for live-insertion applications using  $I_{off}$ , power-up 3-state, and BIAS  $V_{CC}$ . The  $I_{off}$  circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down. The power-up 3-state circuitry places the outputs in the high-impedance state during power up and power down, which prevents driver conflict. The BIAS  $V_{CC}$  circuitry precharges and preconditions the B-port input/output connections, preventing disturbance of active data on the backplane during card insertion or removal, and permits true live-insertion capability.

This GTLP device features TI-OPC circuitry, which actively limits overshoot caused by improperly terminated backplanes, unevenly distributed cards, or empty slots during low-to-high signal transitions. This improves signal integrity, which allows adequate noise margin to be maintained at higher frequencies.

High-drive GTLP backplane interface devices feature adjustable edge-rate control (ERC). Changing the ERC input voltage between GND and  $V_{CC}$  adjusts the B-port output rise and fall times. This allows the designer to optimize system data-transfer rate and signal integrity to the backplane load.

Active bus-hold circuitry holds unused or undriven LVTTL data inputs at a valid logic state. Use of pullup or pulldown resistors with the bus-hold circuitry is not recommended.

When  $V_{CC}$  is between 0 and 1.5 V, the device is in the high-impedance state during power up or power down. However, to ensure the high-impedance state above 1.5 V, the output-enable  $(\overline{OE})$  input should be tied to  $V_{CC}$  through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

### ORDERING INFORMATION

TA	PACKAGE†		ORDERABLE PART NUMBER	TOP-SIDE MARKING	
–40°C to 85°C	TSSOP – DGG Tape and reel		SN74GTLPH1655DGGR	GTLPH1655	

<sup>†</sup> Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.



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### functional description

The SN74GTLPH1655 is a high-drive (100 mA), 16-bit UBT transceiver containing D-type latches and D-type flip-flops for data-path operation in transparent, latched, or clocked modes. The device is uniquely partitioned as two 8-bit transceivers with individual latch timing and output signals and a common clock for both transceiver words. It can replace any of the functions shown in Table 1. Data polarity is noninverting.

Table 1. SN74GTLPH1655 UBT Transceiver Replacement Functions

FUNCTION	8 BIT	9 BIT	10 BIT	16 BIT
Transceiver	'245, '623, '645	'863	'861	'16245, '16623
Buffer/driver	'241, '244, '541		'827	'16241, '16244, '16541
Latched transceiver	'543			'16543
Latch	'373, '573	'843	'841	'16373
Registered transceiver	'646, '652			'16646, '16652
Flip-flop	'374, '574		'821	'16374
SN74GTLPH1655 UBT transceiver replaces all above functions				

Data flow for each word is determined by the respective latch enables (xLEAB and xLEBA), output enables (xOEAB and xOEBA), and clock (CLK). The output enables (1OEAB, 1OEBA, 2OEAB, and 2OEBA) control byte 1 and byte 2 data for the A-to-B and B-to-A directions, respectively. Note that CLK is common to both directions and both 8-bit words. OE also is common and disables all I/O ports simultaneously.

For A-to-B data flow, the devices operate in the transparent mode when LEAB is high. When LEAB transitions low, the A data is latched independent of CLK high or low. If LEAB is low, the A data is registered on the CLK low-to-high transition. When  $\overline{OEAB}$  is low, the outputs are active. With  $\overline{OEAB}$  high, the outputs are in the high-impedance state.

The data flow for the B-to-A direction is identical, except  $\overline{\text{OEBA}}$ , LEBA, and CLK are used.

#### **Function Tables**

### FUNCTION†

	INPUTS				MODE	
OEAB	LEAB	CLK	Α	В	WODE	
Н	Χ	Х	Х	Z	Isolation	
L	L	Н	Х	в <sub>0</sub> ‡	Latabad storage of A data	
L	L	L	Χ	В <sub>0</sub> ‡ В <sub>0</sub> §	Latched storage of A data	
L	Н	Х	L	L	True transparent	
L	Н	X	Н	Н	True transparent	
L	L	1	L	L	Clasked storage of A data	
L	L	1	Н	Н	Clocked storage of A data	

<sup>†</sup> A-to-B data flow is shown. B-to-A flow is similar, but uses OEBA, LEBA, and CLK. The condition when OEAB and OEBA are both low at the same time is not recommended.



<sup>‡</sup>Output level before the indicated steady-state input conditions were established, provided that CLK was high before LEAB went low

<sup>§</sup> Output level before the indicated steady-state input conditions were established

### **Function Tables (Continued)**

### **OUTPUT ENABLE**

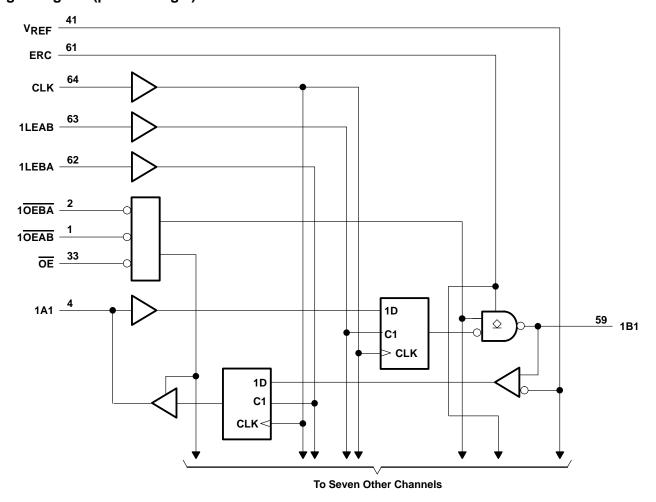
INPUTS			OUTI	PUTS
ŌĒ	OEAB	OEBA	A PORT	B PORT
L	L	L	Active	Active†
L	L	Н	Z	Active
L	Н	L	Active	Z
L	Н	Н	Z	Z
Н	X	X	Z	Z

<sup>†</sup> This condition is not recommended.

### **B-PORT EDGE-RATE CONTROL (ERC)**

INPU	JT ERC	OUTPUT		
LOGIC NOMINAL LEVEL VOLTAGE		B-PORT EDGE RATE		
Н	Vcc	Slow		
L	GND	Fast		

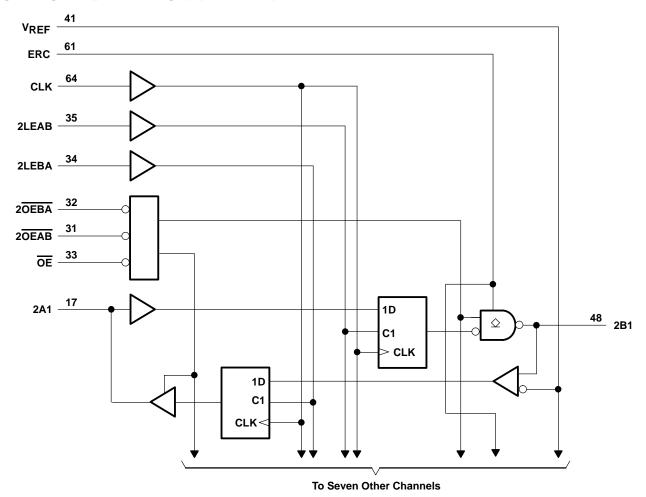
## logic diagram (positive logic)





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## logic diagram (positive logic) (continued)





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### absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V <sub>CC</sub> and BIAS V <sub>CC</sub>	–0.5 V to 4.6 V
Input voltage range, V <sub>I</sub> (see Note 1): A port, ERC, and control inputs	–0.5 V to 7 V
B port and V <sub>REF</sub>	–0.5 V to 4.6 V
Voltage range applied to any output in the high-impedance or power-off state, VO	
(see Note 1): A port	–0.5 V to 7 V
B port	–0.5 V to 4.6 V
Current into any output in the low state, I <sub>O</sub> : A port	48 mA
B port	200 mA
Current into any A port output in the high state, IO (see Note 2)	48 mA
Continuous current through each V <sub>CC</sub> or GND	±100 mA
Input clamp current, I <sub>IK</sub> (V <sub>I</sub> < 0)	
Output clamp current, I <sub>OK</sub> (V <sub>O</sub> < 0)	–50 mA
Package thermal impedance, θ <sub>JA</sub> (see Note 3)	55°C/W
Storage temperature range, T <sub>stg</sub>	–65°C to 150°C

<sup>†</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
  - 2. This current flows only when the output is in the high state and  $V_O > V_{CC}$ .
  - 3. The package thermal impedance is calculated in accordance with JESD 51-7.



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### recommended operating conditions (see Notes 4 through 7)

			MIN	NOM	MAX	UNIT
V <sub>CC</sub> , BIAS V <sub>CC</sub>	Supply voltage		3.15	3.3	3.45	V
\/	Termination valtage	GTL	1.14	1.2	1.26	V
VTT	Termination voltage	GTLP	1.35	1.5	1.65	V
V	Reference voltage	GTL	0.74	0.8	0.87	V
VREF	Reference voltage	GTLP	0.87	1	1.1	V
V.	Input voltage	B port			$V_{TT}$	V
V <sub>I</sub>	Input voltage	Except B port		Vcc	5.5	V
		B port	V <sub>REF</sub> +0.05			
$V_{IH}$	High-level input voltage	ERC	V <sub>CC</sub> -0.6	Vcc	5.5	V
		Except B port and ERC	2			
	Low-level input voltage	B port			V <sub>REF</sub> -0.05	
$V_{IL}$		ERC		GND	0.6	V
		Except B port and ERC			0.8	
lik	Input clamp current	-			-18	mA
loн	High-level output current	A port			-24	mA
	Law lavel autant arreset	A port			24	A
IOL	Low-level output current	B port			100	mA
Δt/Δν	Input transition rise or fall rate	Outputs enabled			10	ns/V
Δt/ΔV <sub>CC</sub>	Power-up ramp rate	•	20			μs/V
TA	Operating free-air temperature		-40		85	°C

- NOTES: 4. All unused control and B-port inputs of the device must be held at V<sub>CC</sub> or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.
  - 5. Proper connection sequence for use of the B-port I/O precharge feature is GND and BIAS V<sub>CC</sub> = 3.3 V first, I/O second, and V<sub>CC</sub> = 3.3 V last, because the BIAS V<sub>CC</sub> precharge circuitry is disabled when any V<sub>CC</sub> pin is connected. The control and V<sub>REF</sub> inputs can be connected anytime, but normally are connected during the I/O stage. If B-port precharge is not required, any connection sequence is acceptable, but generally, GND is connected first.
  - 6. V<sub>TT</sub> and R<sub>TT</sub> can be adjusted to accommodate backplane impedances if the dc recommended I<sub>OL</sub> ratings are not exceeded.
  - V<sub>REF</sub> can be adjusted to optimize noise margins, but normally is two-thirds V<sub>TT</sub>. TI-OPC circuitry is enabled in the A-to-B direction and is activated when V<sub>TT</sub> > 0.7 V above V<sub>REF</sub>. If operated in the A-to-B direction, V<sub>REF</sub> should be set to within 0.6 V of V<sub>TT</sub> to minimize current drain.



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## electrical characteristics over recommended operating free-air temperature range for GTLP (unless otherwise noted)

PARAMETER		TEST CONDITIONS			TYP†	MAX	UNIT	
VIK		V <sub>CC</sub> = 3.15 V,	I <sub>I</sub> = -18 mA		-	-1.2	V	
		V <sub>CC</sub> = 3.15 V to 3.45 V,	I <sub>OH</sub> = -100 μA	V <sub>CC</sub> -0.2	-			
V <sub>OH</sub> A port	V 2.45 V	I <sub>OH</sub> = -12 mA	2.4			V		
		V <sub>CC</sub> = 3.15 V	I <sub>OH</sub> = -24 mA	2				
		$V_{CC} = 3.15 \text{ V to } 3.45 \text{ V},$	I <sub>OL</sub> = 100 μA			0.2		
	A port	V <sub>CC</sub> = 3.15 V	I <sub>OL</sub> = 12 mA			0.4		
VOL		VCC = 3.13 V	I <sub>OL</sub> = 24 mA			0.5	٧	
VOL			$I_{OL} = 10 \text{ mA}$			0.2	V	
	B port $V_{CC} = 3.15 \text{ V}$	V <sub>CC</sub> = 3.15 V	I <sub>OL</sub> = 64 mA			0.4		
			I <sub>OL</sub> = 100 mA			0.55	55	
lį	Control inputs	$V_{CC} = 3.45 \text{ V},$	$V_{I} = 0 \text{ or } 5.5 \text{ V}$			±10	μΑ	
. +	A port	V <sub>CC</sub> = 3.45 V	VO = VCC			10	μΑ	
IOZH <sup>‡</sup>	B port		V <sub>O</sub> = 1.5 V		-	10		
lozL <sup>‡</sup>	A and B ports	V <sub>CC</sub> = 3.45 V,	V <sub>O</sub> = GND			-10	μΑ	
I <sub>BHL</sub> §	A port	V <sub>CC</sub> = 3.15 V,	V <sub>I</sub> = 0.8 V	75			μΑ	
I <sub>BHH</sub> ¶	A port	V <sub>CC</sub> = 3.15 V,	V <sub>I</sub> = 2 V	<b>-</b> 75			μΑ	
I <sub>BHLO</sub> #	A port	V <sub>CC</sub> = 3.45 V,	$V_I = 0$ to $V_{CC}$	500			μΑ	
Івнно	A port	V <sub>CC</sub> = 3.45 V,	$V_I = 0$ to $V_{CC}$	-500			μΑ	
		V <sub>CC</sub> = 3.45 V, I <sub>O</sub> = 0,	Outputs high			40		
Icc	A or B port	$V_I$ (A-port or control input) = $V_{CC}$ or GND,	Outputs low			40	mA	
		$V_I$ (B port) = $V_{TT}$ or GND	Outputs disabled			40		
Δl <sub>CC</sub> ≉		V <sub>CC</sub> = 3.45 V, One A-port or control input at Other A-port or control inputs at V <sub>CC</sub> or GNI				1.5	mA	
Ci	Control inputs	V <sub>I</sub> = 3.15 V or 0			4.5	6.5	pF	
C.	A port	V <sub>O</sub> = 3.15 V or 0			6.5	7.5	~F	
C <sub>io</sub>	B port	V <sub>O</sub> = 1.5 V or 0			8.5	10.5	pF	

<sup>&</sup>lt;sup>†</sup> All typical values are at  $V_{CC} = 3.3 \text{ V}$ ,  $T_A = 25^{\circ}\text{C}$ .

### hot-insertion specifications for A port over recommended operating free-air temperature range

PARAMETER	TEST CONDITIONS			MIN	MAX	UNIT
l <sub>off</sub>	$V_{CC} = 0$ ,	BIAS $V_{CC} = 0$ ,	$V_{I}$ or $V_{O} = 0$ to 5.5 V		10	μΑ
lozpu	$V_{CC} = 0 \text{ to } 1.5 \text{ V},$	$V_0 = 0.5 V \text{ to } 3 V,$	OE = 0		±30	μΑ
IOZPD	$V_{CC} = 1.5 \text{ V to } 0,$	$V_0 = 0.5 \text{ V to 3 V},$	OE = 0		±30	μΑ



For I/O ports, the parameters I<sub>OZH</sub> and I<sub>OZL</sub> include the input leakage current.

<sup>§</sup> The bus-hold circuit can sink at least the minimum low sustaining current at V<sub>IL</sub>max. I<sub>BHL</sub> should be measured after lowering V<sub>IN</sub> to GND and then raising it to V<sub>IL</sub>max.

The bus-hold circuit can source at least the minimum high sustaining current at V<sub>IH</sub>min. I<sub>BHH</sub> should be measured after raising V<sub>IN</sub> to V<sub>CC</sub> and then lowering it to V<sub>IH</sub>min.

 $<sup>^{\#}\</sup>mbox{An external driver must source}$  at least  $\mbox{I}_{\mbox{BHLO}}$  to switch this node from low to high.

An external driver must sink at least IBHHO to switch this node from high to low.

<sup>\*</sup>This is the increase in supply current for each input that is at the specified TTL voltage level rather than V<sub>CC</sub> or GND.

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## live-insertion specifications for B port over recommended operating free-air temperature range

PARAMETER		TEST CONDITIONS			MAX	UNIT
loff	$V_{CC} = 0$ ,	BIAS $V_{CC} = 0$ ,	$V_I$ or $V_O = 0$ to 1.5 $V$		10	μΑ
lozpu	$V_{CC} = 0 \text{ to } 1.5 \text{ V},$	BIAS $V_{CC} = 0$ ,	$V_0 = 0.5 \text{ V to } 1.5 \text{ V}, \overline{OE} = 0$		±30	μΑ
lozpd	$V_{CC} = 1.5 \text{ V to } 0,$	BIAS $V_{CC} = 0$ ,	$V_0 = 0.5 \text{ V to } 1.5 \text{ V}, \overline{OE} = 0$		±30	μΑ
log (PIAS Voc)	$V_{CC} = 0 \text{ to } 3.15 \text{ V}$	BIAS V <sub>CC</sub> = 3.15 V to 3.45 V,	V <sub>O</sub> (B port) = 0 to 1.5 V		5	mA
ICC (BIAS VCC)	V <sub>CC</sub> = 3.15 V to 3.45 V				10	μΑ
VO	$V_{CC} = 0$ ,	BIAS V <sub>CC</sub> = 3.3 V	IO = 0	0.95	1.05	V
IO	$V_{CC} = 0$ ,	BIAS $V_{CC} = 3.15 \text{ V to } 3.45 \text{ V}$ ,	V <sub>O</sub> (B port) = 0.6 V	-1	·	μΑ

# timing requirements over recommended ranges of supply voltage and operating free-air temperature, $V_{TT}$ = 1.5 V and $V_{REF}$ = 1 V for GTLP (unless otherwise noted)

			MIN	MAX	UNIT
fclock	f <sub>clock</sub> Clock frequency				MHz
	Pulse duration	LEAB or LEBA high	3		ns
t <sub>W</sub>	T GIOC GGTGHOTT	CLK high or low	3		115
	A. Cohun kima	A before CLK	3		
۱.		B before CLK	3		
t <sub>su</sub>	Setup time	A before LEAB↓, CLK = don't care	2.5		ns
		B before LEBA↓, CLK = don't care	2.5		
		A after CLK	0.5		
<b>.</b>	Hold time	B after CLK	0.5		20
t <sub>h</sub>	noia line	A after LEAB↓, CLK = don't care	0.5		ns
		B after LEBA↓, CLK = don't care	0.5		

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# switching characteristics over recommended ranges of supply voltage and operating free-air temperature, $V_{TT}$ = 1.5 V and $V_{REF}$ = 1 V for GTLP (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	EDGE RATET	MIN	TYP‡ MAX	UNIT	
f <sub>max</sub>				175		MHz	
<sup>t</sup> PLH	А	В	Slow	3.5	7.7	ns	
<sup>t</sup> PHL	Α			2.4	6.3		
<sup>t</sup> PLH	А	В	Fast	2	6.3	ns	
<sup>t</sup> PHL	χ			2	5.9		
<sup>t</sup> PLH	LEAB	В	Slow	3.5	7.8	ns	
<sup>t</sup> PHL	LLAD			2.7	6.4		
<sup>t</sup> PLH	LEAB	В	Fast	2	6.4	ns	
<sup>t</sup> PHL	LLAD			2	6		
<sup>t</sup> PLH	CLK	В	Slow	4.7	8	ns	
<sup>t</sup> PHL	CLK			2.7	6.4		
<sup>t</sup> PLH	CLK	В	Fast	3.6	6.8	ns	
<sup>t</sup> PHL	CLK			2	6.1		
t <sub>en</sub>	<del></del>	В	Slow	3.5	7.3	ns	
<sup>t</sup> dis	ŌĒ			3.5	7		
t <sub>en</sub>		В	Fast	2	6	ns	
<sup>t</sup> dis	ŌĒ			2	6.6		
t <sub>en</sub>	OEAB	В	Slow	3.5	7.4	ns	
<sup>t</sup> dis				3.5	7		
t <sub>en</sub>	0545	В	Fast	2	6.1	ns	
<sup>t</sup> dis	OEAB			2	6.3		
	Rise time, B outputs (20% to 80%)		Slow		2.6	ns	
t <sub>r</sub>			Fast		1.5		
4.	Fall time, B outputs (80% to 20%)		Slow		3	no	
t <sub>f</sub>	rali time, b outpo	uis (80% to 20%)	Fast	2.2		ns	
<sup>t</sup> PLH	В	А	_	1.5	5.5	ns	
<sup>t</sup> PHL	Ь			1.5	5.5		
<sup>t</sup> PLH	LEBA	А	-	1.3	5.2	ns	
<sup>t</sup> PHL	LEDA			1	5		
<sup>t</sup> PLH	CLK	А	-	1.2	6.3	ns	
<sup>t</sup> PHL	OLK			1	5		
t <sub>en</sub>	<u> </u>	A	-	1.5	5.6	ns	
<sup>t</sup> dis	ŌĒ	A		1.5	6.1		
t <sub>en</sub>	OED4	А	-	1.2	5.4	ns	
<sup>t</sup> dis	OEBA			2	6.1		

<sup>†</sup> Slow (ERC = V<sub>CC</sub>) and Fast (ERC = GND)

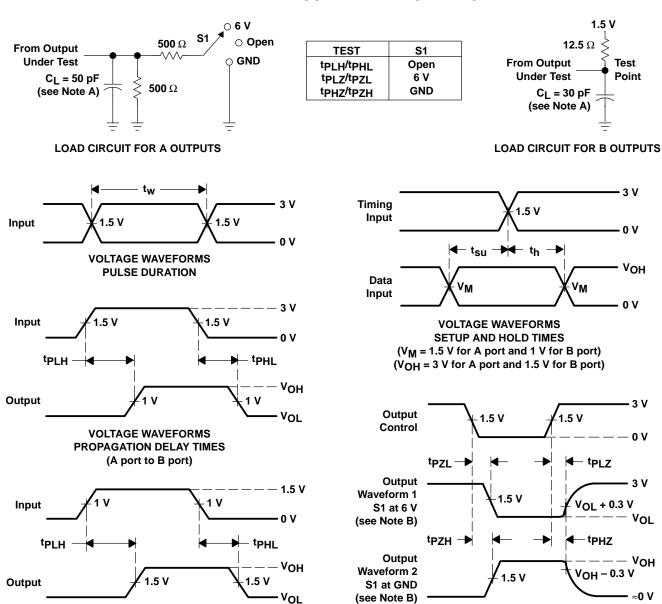


<sup>‡</sup> All typical values are at  $V_{CC} = 3.3 \text{ V}$ ,  $T_A = 25^{\circ}\text{C}$ .

**VOLTAGE WAVEFORMS ENABLE AND DISABLE TIMES** 

(A port)

### PARAMETER MEASUREMENT INFORMATION



NOTES: A. C<sub>I</sub> includes probe and jig capacitance.

**VOLTAGE WAVEFORMS** 

**PROPAGATION DELAY TIMES** (B port to A port)

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR  $\approx$  10 MHz,  $Z_O = 50 \Omega$ ,  $t_f \approx 2$  ns,  $t_f \approx 2$  ns.
- D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuits and Voltage Waveforms



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### DISTRIBUTED-LOAD BACKPLANE SWITCHING CHARACTERISTICS

The preceding switching characteristics table shows the switching characteristics of the device into a lumped load (Figure 1). However, the designer's backplane application probably is a distributed load. The physical representation is shown in Figure 2. This backplane, or distributed load, can be approximated closely to a resistor inductance capacitance (RLC) circuit, as shown in Figure 3. This device has been designed for optimum performance in this RLC circuit. The following switching characteristics table shows the switching characteristics of the device into the RLC load, to help the designer better understand the performance of the GTLP device in this typical backplane. See www.ti.com/sc/gtlp for more information.

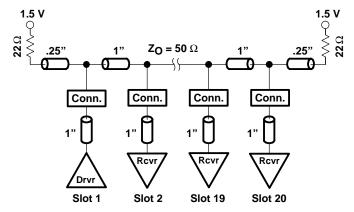


Figure 2. High-Drive Test Backplane

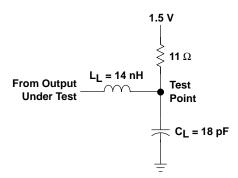


Figure 3. High-Drive RLC Network

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# switching characteristics over recommended ranges of supply voltage and operating free-air temperature, $V_{TT}$ = 1.5 V and $V_{REF}$ = 1 V for GTLP (see Figure 3)

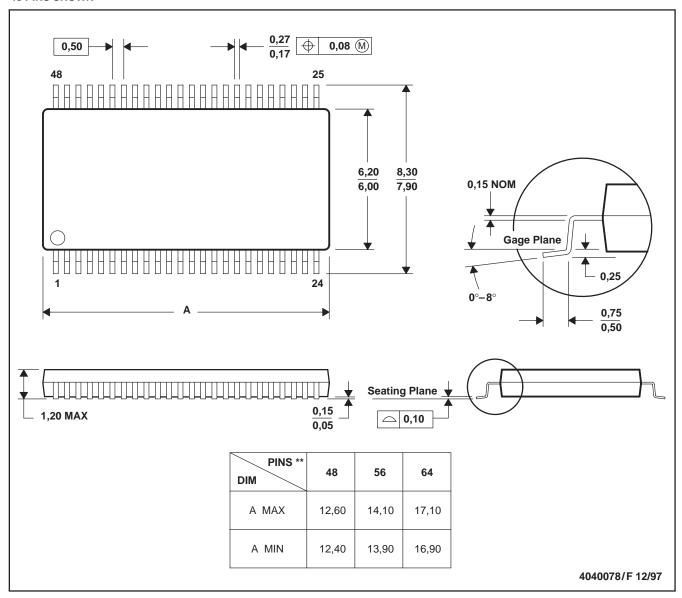
PARAMETER	FROM (INPUT)	TO (OUTPUT)	EDGE RATET	түр‡	UNIT	
<sup>t</sup> PLH	A	В	Slow	5	ns	
<sup>t</sup> PHL	A			5		
<sup>t</sup> PLH	A	В	Fast	3.8	ns	
<sup>t</sup> PHL				3.8		
<sup>t</sup> PLH	LEAB	В	Slow	4.9	ns	
<sup>t</sup> PHL	LLAD			4.9		
<sup>t</sup> PLH	LEAB	В	Fast	3.9	ns	
t <sub>PHL</sub>	LLAD			3.9		
<sup>t</sup> PLH	CLK	В	Slow	4.8	ns	
t <sub>PHL</sub>	OLK			4.8		
<sup>t</sup> PLH	CLK	В	Fast	3.7	ns	
<sup>t</sup> PHL	OEK			3.7		
t <sub>en</sub>	OEAB or OE	В	Slow	4.9	ns	
<sup>t</sup> dis	OLAB OI OL			4.7		
t <sub>en</sub>	OEAB or OE	В	Fast	3.5	ns	
<sup>t</sup> dis	OLAB OI OL			4.1		
t <sub>r</sub>	Rise time, B outputs (20% to 80%)		Slow	2	ns	
	rase time, b outp	Fast	1.2	113		
t <sub>f</sub>	Fall time, B outputs (80% to 20%)		Slow	2.5	ns	
Ч			Fast	1.8	110	

<sup>†</sup> Slow (ERC =  $V_{CC}$ ) and Fast (ERC = GND) ‡ All typical values are at  $V_{CC}$  = 3.3 V,  $T_A$  = 25°C. All values are derived from TI-SPICE models.

## DGG (R-PDSO-G\*\*)

### PLASTIC SMALL-OUTLINE PACKAGE

### **48 PINS SHOWN**



NOTES: A. All linear dimensions are in millimeters.

B. This drawing is subject to change without notice.

C. Body dimensions do not include mold protrusion not to exceed 0,15.

D. Falls within JEDEC MO-153

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